

## PNP SILICON DUAL TRANSISTOR

Qualified per MIL-PRF-19500 /336

### DEVICES

2N3810      2N3811  
 2N3810L    2N3811L  
 2N3810U    2N3811U

### LEVELS

JAN  
 JANTX  
 JANTV  
 JANS

### ABSOLUTE MAXIMUM RATINGS ( $T_C = +25^\circ\text{C}$ unless otherwise noted)

| Parameters / Test Conditions                        | Symbol         | Value                    |                            | Unit             |
|---|----------------|--------------------------|----------------------------|------------------|
| Collector-Emitter Voltage                           | $V_{CEO}$      | 60                       |                            | Vdc              |
| Collector-Base Voltage                              | $V_{CBO}$      | 60                       |                            | Vdc              |
| Emitter-Base Voltage                                | $V_{EBO}$      | 5.0                      |                            | Vdc              |
| Collector Current                                   | $I_C$          | 50                       |                            | mAdc             |
|   |                | One Section <sup>1</sup> | Both Sections <sup>2</sup> |                  |
| Total Power Dissipation @ $T_A = +25^\circ\text{C}$ | $P_T$          | 200                      | 350                        | mW               |
| Operating & Storage Junction Temperature Range      | $T_J, T_{stg}$ | -65 to +200              |                            | $^\circ\text{C}$ |



TO-78

### Note:

1. Derate linearly 1.143mW/ $^\circ\text{C}$  for  $T_A > +25^\circ\text{C}$  (one section)
2. Derate linearly 2.00mW/ $^\circ\text{C}$  for  $T_A > +25^\circ\text{C}$  (both sections)

### ELECTRICAL CHARACTERISTICS ( $T_A = +25^\circ\text{C}$ , unless otherwise noted)

| Parameters / Test Conditions  | Symbol        | Min. | Max.     | Unit                                |
|---|---------------|------|----------|-------------------------------------|
| <b>OFF CHARACTERISTICS</b>  |               |      |          |                                     |
| Collector-Emitter Breakdown Voltage<br>$I_C = 100\mu\text{Adc}$                     | $V_{(BR)CEO}$ | 60   |          | Vdc                                 |
| Collector-Base Cutoff Current<br>$V_{CB} = 50\text{Vdc}$<br>$V_{CB} = 60\text{Vdc}$ | $I_{CBO}$     |      | 10<br>10 | $\eta\text{Adc}$<br>$\mu\text{Adc}$ |
| Emitter-Base Cutoff Current<br>$V_{EB} = 4.0\text{Vdc}$<br>$V_{EB} = 5.0\text{Vdc}$ | $I_{EBO}$     |      | 10<br>10 | $\eta\text{Adc}$<br>$\mu\text{Adc}$ |



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# TECHNICAL DATA SHEET

## PNP SILICON DUAL TRANSISTOR Qualified per MIL-PRF-19500 /336

### ELECTRICAL CHARACTERISTICS (con't)

| Parameters / Test Conditions   | Symbol  | Min.                                 | Max.   | Unit       |
|--|---|--------------------------------------|--|------------|
| <b>ON CHARACTERISTICS</b>  |   |                                      |  |            |
| Forward-Current Transfer Ratio<br>$I_C = 10\mu\text{A dc}, V_{CE} = 5.0\text{V dc}$<br>$I_C = 100\mu\text{A dc}, V_{CE} = 5.0\text{V dc}$<br>$I_C = 1.0\text{mA dc}, V_{CE} = 5.0\text{V dc}$<br>$I_C = 10\text{mA dc}, V_{CE} = 5.0\text{V dc}$<br><br>$I_C = 1.0\mu\text{A dc}, V_{CE} = 5.0\text{V dc}$<br>$I_C = 10\mu\text{A dc}, V_{CE} = 5.0\text{V dc}$<br>$I_C = 100\mu\text{A dc}, V_{CE} = 5.0\text{V dc}$<br>$I_C = 1.0\text{mA dc}, V_{CE} = 5.0\text{V dc}$<br>$I_C = 10\text{mA dc}, V_{CE} = 5.0\text{V dc}$ | 2N3810, 2N3810L , 2N3810U<br><br><br><br><br>2N3811, 2N3811L, 2N3811U | $h_{FE}$<br><br><br><br><br>$h_{FE}$ | 100<br>150<br>150<br>125<br><br>75<br>225<br>300<br>300<br>250 | 450<br>450 |
| Collector-Emitter Saturation Voltage<br>$I_C = 100\mu\text{A dc}, I_B = 10\mu\text{A dc}$<br>$I_C = 1.0\text{mA dc}, I_B = 100\mu\text{A dc}$  | $V_{CE(sat)}$   |                                      | 0.2<br>0.25  | Vdc        |
| Base-Emitter Saturation Voltage<br>$I_C = 100\mu\text{A dc}, I_B = 10\mu\text{A dc}$<br>$I_C = 1.0\text{mA dc}, I_B = 100\mu\text{A dc}$   | $V_{BE(sat)}$   |                                      | 0.7<br>0.8   | Vdc        |
| Base-Emitter Non-Saturation Voltage<br>$V_{CE} = 5.0\text{A dc}, I_C = 100\mu\text{A dc}$  | $V_{BE}$  |                                      | 0.7  | Vdc        |

### DYNAMIC CHARACTERISTICS

|  |            |  |            |                        |
|--|------------|--|------------|------------------------|
| Forward Current Transfer Ratio, Magnitude<br>$I_C = 500\mu\text{A dc}, V_{CE} = 5.0\text{V dc}, f = 30\text{MHz}$<br>$I_C = 1.0\text{mA dc}, V_{CE} = 5.0\text{V dc}, f = 100\text{MHz}$ | $ h_{fe} $ | 1.0<br>1.0   | 5.0        |                        |
| Small-Signal Short Circuit Forward Current Transfer Ratio<br>$I_C = 1.0\text{mA dc}, V_{CE} = 10\text{V dc}, f = 1.0\text{kHz}$  | $h_{fe}$   | 2N3810, 2N3810L , 2N3810U<br>2N3811, 2N3811L , 2N3811U | 150<br>300 | 600<br>900             |
| Small-Signal Short Circuit Input Impedance<br>$I_C = 1.0\text{mA dc}, V_{CE} = 10\text{V dc}, f = 1.0\text{kHz}$   | $h_{je}$   | 2N3810, 2N3810L , 2N3810U<br>2N3811, 2N3811L , 2N3811U | 3.0<br>3.0 | 30<br>40<br>k $\Omega$ |
| Small-Signal Short Circuit Output Admittance<br>$I_C = 1.0\text{mA dc}, V_{CE} = 10\text{V dc}, f = 1.0\text{kHz}$   | $h_{oe}$   | 2N3810, 2N3810L , 2N3810U<br>2N3811, 2N3811L , 2N3811U | 5.0        | 60<br>$\mu\text{mhos}$ |
| Output Capacitance<br>$V_{CB} = 5.0\text{V dc}, I_E = 0, 100\text{kHz} \leq f \leq 1.0\text{MHz}$  | $C_{obo}$  |  | 5.0        | pF                     |
| Input Capacitance<br>$V_{EB} = 5.0\text{V dc}, I_C = 0, 100\text{kHz} \leq f \leq 1.0\text{MHz}$   | $C_{lbo}$  |  | 8.0        | pF                     |